

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







256K X 8 BIT LOW POWER CMOS SRAM

FEATURES

Access time: 55ns
Low power consumption:
Operating current: 20mA (TYP.)

Standby current : 20mA(TYP.)L Version

1μA (TYP.) LL-version

■ Single 2.7V ~ 3.6V power supply

■ Fully static operation

■ Tri-state output

Data retention voltage : 1.5V (MIN.)
All Products ROHS Compliant

■ Package: 32-pin 450 mil SOP

32-pin 8mm x 20mm TSOP-I 32-pin 8mm x 13.4mm sTSOP 36-ball 6mm x 8mm TFBGA

GENERAL DESCRIPTION

The AS6C2008 is a 2,097,152-bit low power CMOS static random access memory organized as 262,144 words by 8 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

The AS6C2008 is well designed for very low power system applications, and particularly well suited for battery back-up nonvolatile memory application.

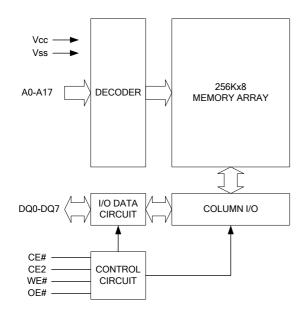
The AS6C2008 operates from a single power supply of $2.7V \sim 3.6V$

.

PRODUCT FAMILY

Product	Operating	Vcc Range	Speed	Speed Power Dissipation		
Family	Temperature	vcc range	Оресси	Standby(IsB1,TYP.)	Operating(Icc,TYP.)	
AS6C2008 (I)	-40 ~ 85°C	2.7 ~ 3.6V	55ns	20μA(L)/1μA(LL)	20mA	

FUNCTIONAL BLOCK DIAGRAM

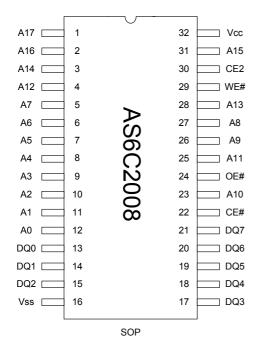


PIN DESCRIPTION

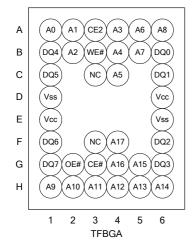
SYMBOL	DESCRIPTION
A0 - A17	Address Inputs
DQ0 – DQ7	Data Inputs/Outputs
CE#, CE2	Chip Enable Inputs
WE#	Write Enable Input
OE#	Output Enable Input
Vcc	Power Supply
Vss	Ground
NC	No Connection

256K X 8 BIT LOW POWER CMOS SRAM

PIN CONFIGURATION







256K X 8 BIT LOW POWER CMOS SRAM

ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to Vss	VTERM	-0.5 to 4.6	V
Operating Temperature	Та	-40 to 85(I grade)	°C
Storage Temperature	Тѕтс	-65 to 150	°C
Power Dissipation	PD	1	W
DC Output Current	Іоит	50	mA
Soldering Temperature (under 10 sec)	Tsolder	260	°C

^{*}Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE#	CE2	OE#	WE#	I/O OPERATION	SUPPLY CURRENT
Standby	Н	Х	Х	Х	High-Z	Isb,Isb1
Stariuby	Х	L	Х	Х	High-Z	ISB,ISB1
Output Disable	L	Н	Н	Н	High-Z	lcc,lcc1
Read	L	Н	L	Н	D оит	lcc,lcc1
Write	L	Н	Х	L	Din	lcc,lcc1

Note: H = VIH, L = VIL, X = Don't care.

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDIT	MIN.	TYP. *4	MAX.	UNIT	
Supply Voltage	Vcc			2.7	3.0	3.6	V
Input High Voltage	V _{IH} *1			2.2	-	Vcc+0.3	V
Input Low Voltage	V _{IL} *2			- 0.2	-	0.6	V
Input Leakage Current	ILI	$V_{CC} \ge V_{IN} \ge V_{SS}$		- 1	-	1	μA
Output Leakage Current	ILO	Vcc ≧ Voυτ ≧ Vss, Output Disabled		- 1	-	1	μA
Output High Voltage	Vон	I _{OH} = -1mA	I _{OH} = -1mA			-	V
Output Low Voltage	Vol	I _{OL} = 2mA		-	-	0.4	V
Average Operating	Icc	Cycle time = Min. CE# = V_{IL} and CE2 = $I_{I/O}$ = 0mA	VIH, - 55	-	20	35	mA
Power supply Current	lcc1	Cycle time = 1μ s CE# \leq 0.2V and CE2 \leq 1 μ O = 0mA other pins at 0.2V or \leq	·	-	4	5	mA
	Isa	CE# = V _{IH} or CE2 = V	ľL	-	0.3	0.5	mΑ
Standby Power Supply Current	ISB1	CE# ≧Vcc-0.2V or CE2≦0.2V	- - - *	-	1	20*5	μA

^{*}I= Industrial temperature



256K X 8 BIT LOW POWER CMOS SRAM

Notes:

- 1. $V_{IH}(max) = V_{CC} + 3.0V$ for pulse width less than 10ns.
- 2. VIL(min) = Vss 3.0V for pulse width less than 10ns.
- 3. Over/Undershoot specifications are characterized, not 100% tested.
- 4. Typical values are included for reference only and are not guaranteed or tested. Typical valued are measured at $V_{CC} = V_{CC}(TYP.)$ and $T_A = 25$ °C
- 5. 10µA for special request

CAPACITANCE (TA = 25° C, f = 1.0MHz)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	Cin	-	6	pF
Input/Output Capacitance	Ci/o	-	8	pF

Note: These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0.2V to Vcc - 0.2V
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 30pF + 1TTL$, $I_{OH}/I_{OL} = -1mA/2mA$

AC ELECTRICAL CHARACTERISTICS

(1) READ CYCLE

PARAMETER	SYM	AS6C2	2008-55		UNIT
		MIN	MAX.		
Read Cycle Time	trc	55	-		ns
Address Access Time	taa	-	55		ns
Chip Enable Access Time	t ACE	-	55		ns
Output Enable Access Time	toe	-	30		ns
Chip Enable to Output in Low-Z	tclz*	10	-		ns
Output Enable to Output in Low-Z	tolz*	5	-		ns
Chip Disable to Output in High-Z	tcHz*	-	20		ns
Output Disable to Output in High-Z	tonz*	-	20		ns
Output Hold from Address Change	tон	10	-		ns

(2) WRITE CYCLE

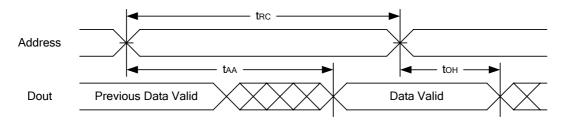
PARAMETER	SYM	AS6C	2008-55		UNIT
		MIN	MAX.		
Write Cycle Time	twc	55	-		ns
Address Valid to End of Write	taw	50	-		ns
Chip Enable to End of Write	tcw	50	-		ns
Address Set-up Time	tas	0	-		ns
Write Pulse Width	twp	45	-		ns
Write Recovery Time	twr	0	-		ns
Data to Write Time Overlap	tow	25	-		ns
Data Hold from End of Write Time	tон	0	-		ns
Output Active from End of Write	tow*	5	-		ns
Write to Output in High-Z	twnz*	-	20		ns

^{*}These parameters are guaranteed by device characterization, but not production tested.

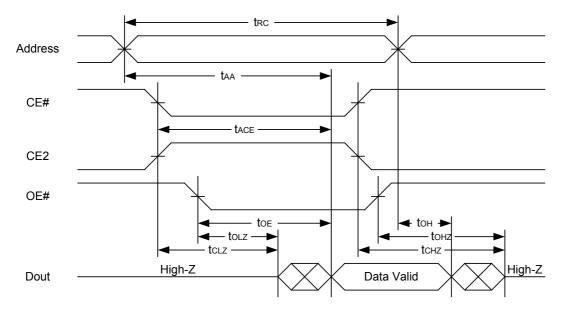
256K X 8 BIT LOW POWER CMOS SRAM

TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



READ CYCLE 2 (CE# and CE2 and OE# Controlled) (1,3,4,5)

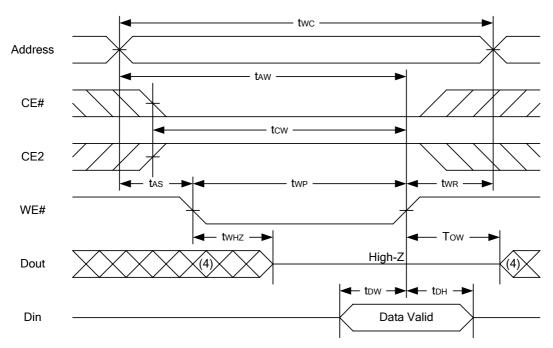


Notes :

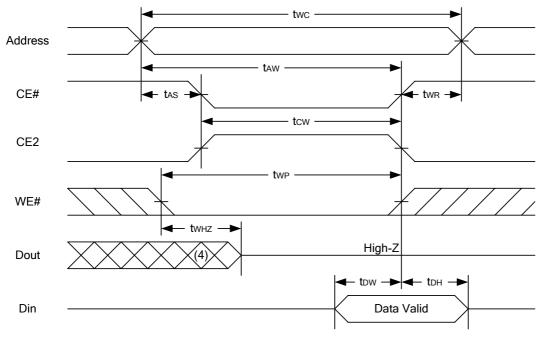
- 1.WE# is high for read cycle.
- 2.Device is continuously selected OE# = low, CE# = low., CE2 = high.
- 3.Address must be valid prior to or coincident with CE# = low, CE2 = high; otherwise tAA is the limiting parameter.
- 4.tclz, tolz, tchz and tohz are specified with CL = 5pF. Transition is measured ±500mV from steady state.
- 5.At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} , t_{OHZ} is less than t_{OLZ} .

256K X 8 BIT LOW POWER CMOS SRAM

WRITE CYCLE 1 (WE# Controlled) (1,2,3,5,6)



WRITE CYCLE 2 (CE# and CE2 Controlled) (1,2,5,6)



Notes:

- 1.WE#, CE# must be high or CE2 must be low during all address transitions.
- 2.A write occurs during the overlap of a low CE#, high CE2, low WE#.
- 3.During a WE#controlled write cycle with OE# low, twp must be greater than twHz + tow to allow the drivers to turn off and data to be placed on the bus.
- 4. During this period, I/O pins are in the output state, and input signals must not be applied.
- 5.If the CE#low transition and CE2 high transition occurs simultaneously with or after WE# low transition, the outputs remain in a high impedance state.
- 6.tow and twHz are specified with C_{L} = 5pF. Transition is measured $\pm 500\text{mV}$ from steady state.

Rev. 1.1 256K X 8 BIT LOW POWER CMOS SRAM

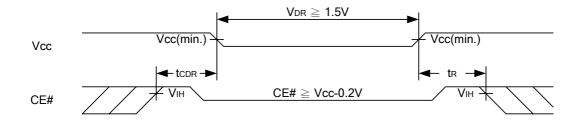
DATA RETENTION CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDI	TION	MIN.	TYP.	MAX.	UNIT
Vcc for Data Retention		$\begin{array}{l} \text{CE\#} \geqq \text{V}_{\text{CC}} \text{- } 0.2\text{V} \\ \text{or CE2} \leqq 0.2\text{V} \end{array}$	_	1.5	-	3.6	V
Data Retention Current		V _{CC} = 1.5V CE# ≧ V _{CC} - 0.2V	-				
	or CE2 ≦	or CE2 ≦ 0.2V	- *	-	0.5	10	μA
Chip Disable to Data Retention Time	I ICDD	See Data Retention Waveforms (below)		0	-	-	ns
Recovery Time	tr			t RC∗	-	-	ns

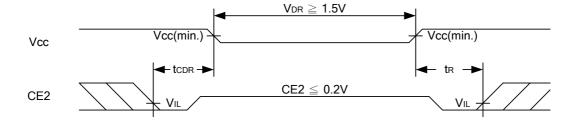
tRC∗ = Read Cycle Time **I= Industrial temperature

DATA RETENTION WAVEFORM

Low Vcc Data Retention Waveform (1) (CE# controlled)

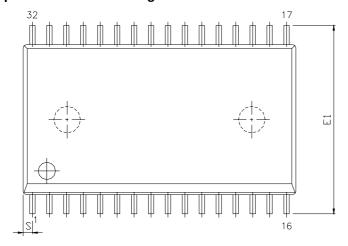


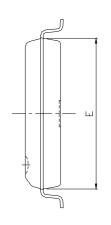
Low Vcc Data Retention Waveform (2) (CE2 controlled)

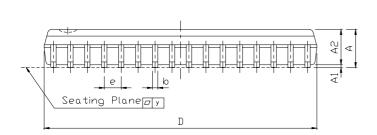


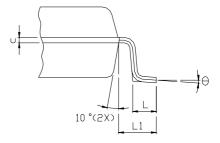
PACKAGE OUTLINE DIMENSION

32 pin 450 mil SOP Package Outline Dimension





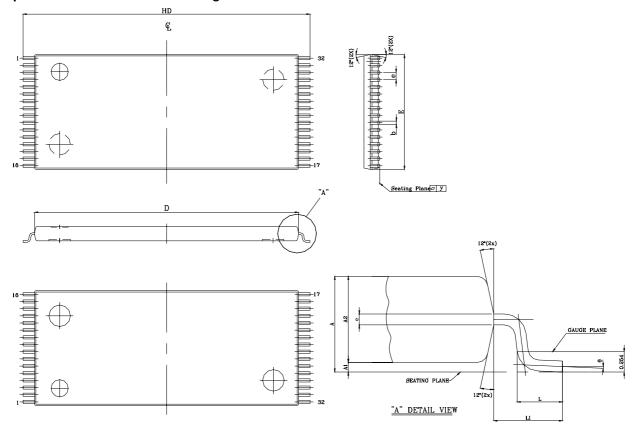




SYM. UNIT	INCH.(BASE)	MM(REF)
Α	0.118 (MAX)	2.997 (MAX)
A1	0.004(MIN)	0.102(MIN)
A2	0.111(MAX)	2.82(MAX)
b	0.016(TYP)	0.406(TYP)
С	0.008(TYP)	0.203(TYP)
D	0.817(MAX)	20.75(MAX)
E	0.445 ±0.005	11.303 ±0.127
E1	0.555 ±0.012	14.097 ±0.305
е	0.050(TYP)	1.270(TYP)
L	0.0347 ±0.008	0.881 ±0.203
L1	0.055 ±0.008	1.397 ±0.203
S	0.026(MAX)	0.660 (MAX)
у	0.004(MAX)	0.101(MAX)
Θ	0° -10°	0° -10°

256K X 8 BIT LOW POWER CMOS SRAM

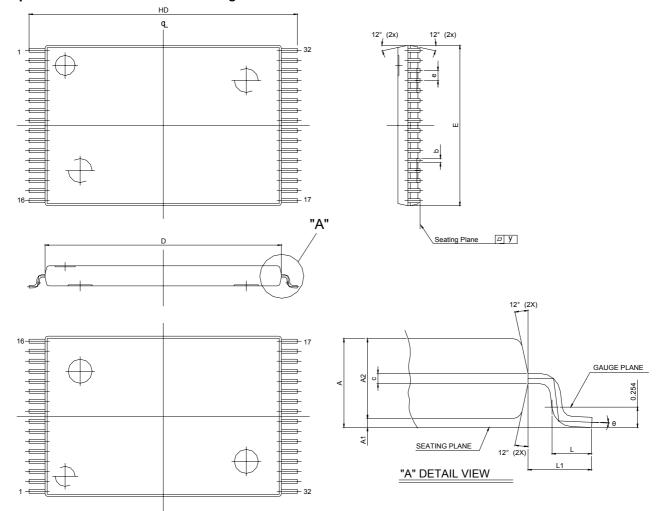
32 pin 8mm x 20mm TSOP-I Package Outline Dimension



SYM. UNIT	INCH(BASE)	MM(REF)
А	0.047 (MAX)	1.20 (MAX)
A1	0.004 ±0.002	0.10 ±0.05
A2	0.039 ±0.002	1.00 ±0.05
b	0.008 + 0.002 - 0.001	0.20 + 0.05 -0.03
С	0.005 (TYP)	0.127 (TYP)
D	0.724 ±0.004	18.40 ±0.10
E	0.315 ±0.004	8.00 ±0.10
е	0.020 (TYP)	0.50 (TYP)
HD	0.787 ±0.008	20.00 ±0.20
L	0.0197 ±0.004	0.50 ±0.10
L1	0.0315 ±0.004	0.08 ±0.10
у	0.003 (MAX)	0.076 (MAX)
Θ	0°∼5°	0°∼5°

256K X 8 BIT LOW POWER CMOS SRAM

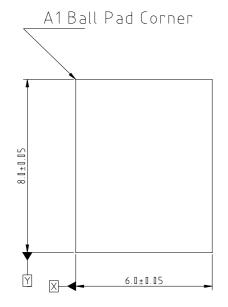
32 pin 8mm x 13.4mm sTSOP Package Outline Dimension

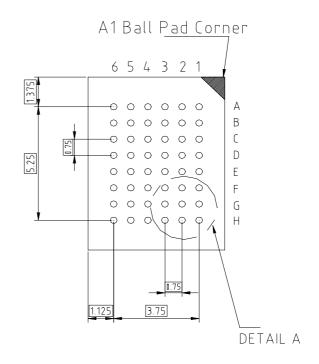


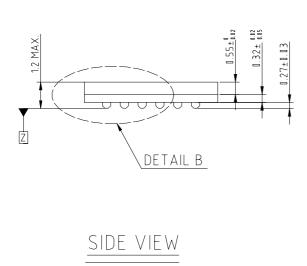
SYM. UNIT	INCH(BASE)	MM(REF)
Α	0.049 (MAX)	1.25 (MAX)
A1	0.005 ±0.002	0.130 ±0.05
A2	0.039 ±0.002	1.00 ±0.05
b	0.008 ±0.01	0.20±0.025
С	0.005 (TYP)	0.127 (TYP)
D	0.465 ±0.004	11.80 ±0.10
E	0.315 ±0.004	8.00 ±0.10
е	0.020 (TYP)	0.50 (TYP)
HD	0.528±0.008	13.40 ±0.20.
L	0.0197 ±0.004	0.50 ±0.10
L1	0.0315 ±0.004	0.8 ±0.10
у	0.003 (MAX)	0.076 (MAX)
Θ	0°~5°	0°~5°

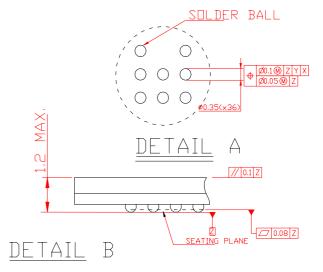
Rev. 1.1 256K X 8 BIT LOW POWER CMOS SRAM

36 ball 6mm × 8mm TFBGA Package Outline Dimension











256K X 8 BIT LOW POWER CMOS SRAM

ORDERING INFORMATION

Ordering Codes

				Operating	Speed
Alliance	Organization	VCC range	Package	Temp	ns
AS6C2008-55SIN	256K X 8	2.7-3.6V	32pin 450mil SOP	Industrial ~ -40°C to 85° C	55
AS6C2008-55TIN	256K X 8	2.7-3.6V	32pin TSOP-I (8 x 20 mm)	Industrial ~ -40°C to 85° C	55
AS6C2008-55STIN	256K X 8	2.7-3.6V	32pin sTSOP (8 x 13.4 mm)	Industrial ~ -40°C to 85° C	55
AS6C2008-55BIN	256K X 8	2.7-3.6V	36pin TFBGA (6mm x 8mm)	Industrial ~ -40°C to 85° C	55

Part numbering system

AS6C	2008	- 55	X	X	N			
			Package Options:	Temperature Range:				
low	Device		S = 32 pin 450 mil SOP	I = Industrial	N = Lead			
power	Number		T = 32 pin TSOP 1 (8mm x 20 mm)	(-40º to +85º C)	Free ROHS			
SRAM	20 = 2M	Access	ST = 32 pin sTSOP (8 x 13.4 mm)		Compliant			
prefix	08 = by 8	Time	B = 36 ball 6 x 8mm TFBGA		Part			

February 2007 AS6C2008





Alliance Memory, Inc. 1116 South Amphlett, #2, San Mateo, CA 94402 Tel: 650-525-3737 Fax: 650-525-0449

www.alliancememory.com

Copyright © Alliance Memory All Rights Reserved

Part Number: AS6C2008 Document Version: v. 1.0

© Copyright 2003 Alliance Memory, Inc. All rights reserved. Our three-point logo, our name and Intelliwatt are trademarks or registered trademarks of Alliance. All other brand and product names may be the trademarks of their respective companies. Alliance reserves the right to make changes to this document and its products at any time without notice. Alliance assumes no responsibility for any errors that may appear in this document. The data contained herein represents Alliance's best data and/or estimates at the time of issuance. Alliance reserves the right to change or correct this data at any time, without notice. If the product described herein is under development, significant changes to these specifications are possible. The information in this product data sheet is intended to be general descriptive information for potential customers and users, and is not intended to operate as, or provide, any guarantee or warrantee to any user or customer. Alliance does not assume any responsibility or liability arising out of the application or use of any product described herein, and disclaims any express or implied warranties related to the sale and/or use of Alliance products including liability or warranties related to fitness for a particular purpose, merchantability, or infringement of any intellectual property rights, except as express agreed to in Alliance's Terms and Conditions of Sale (which are available from Alliance). All sales of Alliance products are made exclusively according to Alliance's Terms and Conditions of Sale. The purchase of products from Alliance does not convey a license under any patent rights, copyrights; mask works rights, trademarks, or any other intellectual property rights of Alliance or third parties. Alliance does not authorize its products for use as critical components in life-supporting systems where a malfunction or failure may reasonably be expected to result in significant injury to the user, and the inclusion of Alliance products in such life-supporting systems implies that